

CD4069UB CMOS Hex Inverter

1 Features

- Standardized Symmetrical Output Characteristics
- Medium Speed Operation: $-t_{PHL}, t_{PLH} = 30$ ns at 10 V (Typical)
- 100% Tested for Quiescent Current at 20 V
- Maximum Input Current of 1 μ A at 18 V Over Full Package-Temperature Range, 100 nA at 18 V and 25°C
- Meets All Requirements of JEDEC Tentative Standard No. 13B, *Standard Specifications for Description of B Series CMOS Devices*

2 Applications

- Logic Inversion
- Pulse Shaping
- Oscillators
- High-Input-Impedance Amplifiers

3 Description

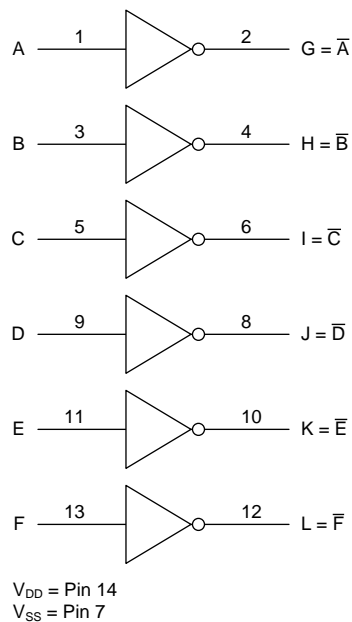
The CD4069UB device consist of six CMOS inverter circuits. These devices are intended for all general-purpose inverter applications where the medium-power TTL-drive and logic-level-conversion capabilities of circuits such as the CD4009 and CD4049 hex inverter and buffers are not required.

Device Information⁽¹⁾

PART NUMBER	PACKAGE (PINS)	BODY SIZE (NOM)
CD4069UBE	PDIP (14)	19.30 mm x 6.35 mm
CD4069UBF	CDIP (14)	19.56 mm x 6.67 mm
CD4069UBM	SOIC (14)	8.65 mm x 3.91 mm
CD4069UBNSR	SO (14)	10.30 mm x 5.30 mm
CD4069UBPW	TSSOP (14)	5.00 mm x 4.40 mm

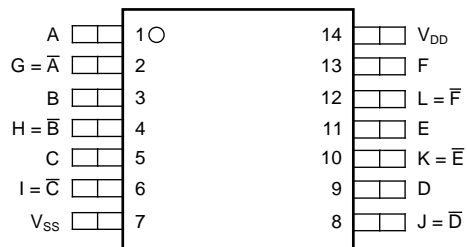
(1) For all available packages, see the orderable addendum at the end of the data sheet.

CD4069UB Functional Diagram



5 Pin Configuration and Functions

D, J, N, NS, and PW Packages
14-Pin PDIP, CDIP, SOIC, SO, and TSSOP
Top View



Pin Functions

PIN		I/O	DESCRIPTION
NAME	NO.		
A	1	I	A input
B	3	I	B input
C	5	I	C input
D	9	I	D input
E	11	I	E input
F	13	I	F input
$G = \bar{A}$	2	O	G output
$H = \bar{B}$	4	O	H output
$I = \bar{C}$	6	O	I output
$J = \bar{D}$	8	O	J output
$K = \bar{E}$	10	O	K output
$L = \bar{F}$	12	O	L output
V_{DD}	14	—	Positive supply
V_{SS}	7	—	Negative supply

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT
V _{DD}	DC supply-voltage (voltages referenced to V _{SS} terminal)	-0.5	20	V
V _I	Input voltage, all inputs	-0.5 to V _{DD}	0.5	V
I _{IK}	DC input current, any one input	-10	10	mA
P _D	Power dissipation per package	-55°C to 100°C	500	mW
		100°C to 125°C	12	
	Device dissipation per output transistor	Full range (all package types)		100
Lead temperature ⁽²⁾			265	°C
T _J	Junction temperature		150	°C
T _{stg}	Storage temperature	-65	150	°C

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) During soldering at distance 1/16 inch ± 1/32 inch (1.59 mm ± 0.79 mm) from case for 10 s maximum

6.2 ESD Ratings

		VALUE	UNIT
V _(ESD)	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±500
		Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±200

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	MAX	UNIT
V _{DD}	Supply voltage	3	18	V
T _A	Operating temperature	-55	125	°C

6.4 Thermal Information

THERMAL METRIC ⁽¹⁾	CD4069UB					UNIT	
	D (SOIC)	J (CDIP)	N (PDIP)	NS (SO)	PW (TSSOP)		
	14 PINS	14 PINS	14 PINS	14 PINS	14 PINS		
R _{θJA}	Junction-to-ambient thermal resistance	94.9	—	57.9	91.2	122.1	°C/W
R _{θJC(top)}	Junction-to-case (top) thermal resistance	56.4	28.5	45.5	48.8	50.8	°C/W
R _{θJB}	Junction-to-board thermal resistance	49.2	—	37.7	50	63.8	°C/W
ψ _{JT}	Junction-to-top characterization parameter	21.1	—	30.6	15	6.3	°C/W
ψ _{JB}	Junction-to-board characterization parameter	48.9	—	37.6	49.6	63.3	°C/W
R _{θJC(bot)}	Junction-to-case (bottom) thermal resistance	N/A	N/A	N/A	N/A	N/A	°C/W

- (1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report, [SPRA953](#).

6.5 Electrical Characteristics – Dynamic

$T_A = 25^\circ\text{C}$; input $t_r, t_f = 20\text{ ns}$; $C_L = 50\text{ pF}$; $R_L = 200\text{ k}\Omega$ (unless otherwise noted)

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t_{PLH}, t_{PHL} Propagation delay time	$V_{DD} (V) = 5$		55	110	ns
	$V_{DD} (V) = 10$		30	60	
	$V_{DD} (V) = 15$		25	50	
t_{THL}, t_{TLH} Transition time	$V_{DD} (V) = 5$		100	200	ns
	$V_{DD} (V) = 10$		50	100	
	$V_{DD} (V) = 15$		40	80	
C_{IN} Input capacitance	Any input		10	15	pF

6.6 Electrical Characteristics – Static

$T_A = 25^\circ\text{C}$; input $t_r, t_f = 20\text{ ns}$; $C_L = 50\text{ pF}$; $R_L = 200\text{ k}\Omega$ (unless otherwise noted)

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
I_{DDmax} Quiescent device current	$V_{IN} = 0V\text{ or }5V, V_{DD} = 5V$	$T_A = -55^\circ\text{C}$		0.25	μA
		$T_A = -40^\circ\text{C}$		0.25	
		$T_A = 25^\circ\text{C}$	0.01	0.25	
		$T_A = 85^\circ\text{C}$		7.5	
		$T_A = 125^\circ\text{C}$		7.5	
		$T_A = 125^\circ\text{C}$		15	
	$V_{IN} = 0\text{ or }10V, V_{DD} = 10V$	$T_A = -55^\circ\text{C}$		0.5	
		$T_A = -40^\circ\text{C}$		0.5	
		$T_A = 25^\circ\text{C}$	0.01	0.5	
		$T_A = 85^\circ\text{C}$		15	
		$T_A = 125^\circ\text{C}$		15	
		$T_A = 125^\circ\text{C}$		15	
	$V_{IN} = 0\text{ or }15V, V_{DD} = 15V$	$T_A = -55^\circ\text{C}$		1	
		$T_A = -40^\circ\text{C}$		1	
		$T_A = 25^\circ\text{C}$	0.01	1	
		$T_A = 85^\circ\text{C}$		30	
		$T_A = 125^\circ\text{C}$		30	
		$T_A = 125^\circ\text{C}$		30	
$V_{IN} = 0\text{ or }20V, V_{DD} = 20V$	$T_A = -55^\circ\text{C}$		5		
	$T_A = -40^\circ\text{C}$		5		
	$T_A = 25^\circ\text{C}$	0.02	5		
	$T_A = 85^\circ\text{C}$		150		
	$T_A = 125^\circ\text{C}$		150		
	$T_A = 125^\circ\text{C}$		150		
I_{OLmin} Output low (sink) current	$V_O = 0.4V, V_{IN} = 5V, V_{DD} = 5V$	$T_A = -55^\circ\text{C}$	0.64		mA
		$T_A = -40^\circ\text{C}$	0.61		
		$T_A = 25^\circ\text{C}$	0.51	1	
		$T_A = 85^\circ\text{C}$	0.42		
		$T_A = 125^\circ\text{C}$	0.36		
		$T_A = 125^\circ\text{C}$	0.36		
	$V_O = 0.5V, V_{IN} = 10V, V_{DD} = 10V$	$T_A = -55^\circ\text{C}$	1.6		
		$T_A = -40^\circ\text{C}$	1.5		
		$T_A = 25^\circ\text{C}$	1.3	2.6	
		$T_A = 85^\circ\text{C}$	1.1		
		$T_A = 125^\circ\text{C}$	0.9		
		$T_A = 125^\circ\text{C}$	0.9		
	$V_O = 1.5V, V_{IN} = 15V, V_{DD} = 15V$	$T_A = -55^\circ\text{C}$	4.2		
		$T_A = -40^\circ\text{C}$	4		
		$T_A = 25^\circ\text{C}$	3.4	6.8	
		$T_A = 85^\circ\text{C}$	2.8		
		$T_A = 125^\circ\text{C}$	2.4		
		$T_A = 125^\circ\text{C}$	2.4		

Electrical Characteristics – Static (continued)

T_A = 25°C; input t_r, t_f = 20 ns; C_L = 50 pF; R_L = 200 kΩ (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
I _{OH} min	Output high (source) current	V _O = 4.6 V, V _{IN} = 0 V, V _{DD} = 5 V	T _A = -55°C	-0.64			mA
			T _A = -40°C	-0.61			
			T _A = 25°C	-0.51	-1		
			T _A = 85°C	-0.42			
			T _A = 125°C	-0.36			
		V _O = 2.5 V, V _{IN} = 0 V, V _{DD} = 5 V	T _A = -55°C	-2			
			T _A = -40°C	-1.8			
			T _A = 25°C	-1.6	-3.2		
			T _A = 85°C	-1.3			
			T _A = 125°C	-1.15			
		V _O = 9.5 V, V _{IN} = 0 V, V _{DD} = 10 V	T _A = -55°C	-1.6			
			T _A = -40°C	-1.5			
			T _A = 25°C	-1.3	-2.6		
			T _A = 85°C	-1.1			
			T _A = 125°C	-0.9			
		V _O = 13.5 V, V _{IN} = 0 V, V _{DD} = 15 V	T _A = -55°C	-4.2			
T _A = -40°C	-4						
T _A = 25°C	-3.4		-6.8				
T _A = 85°C	-2.8						
T _A = 125°C	-2.4						
V _{OL} max	Low-level output voltage	V _{IN} = 5 V, V _{DD} = 5 V	T _A = 25°C		0	0.05	V
			All other temperatures			0.05	
		V _{IN} = 10 V, V _{DD} = 10 V	T _A = 25°C		0	0.05	
			All other temperatures			0.05	
		V _{IN} = 15 V, V _{DD} = 15 V	T _A = 25°C		0	0.05	
			All other temperatures			0.05	
V _{OH} min	High-level output voltage	V _{IN} = 0 V, V _{DD} = 5 V	T _A = 25°C	4.95	5		
			All other temperatures	4.95			
		V _{IN} = 0 V, V _{DD} = 10 V	T _A = 25°C	9.95	10		
			All other temperatures	9.95			
		V _{IN} = 0 V, V _{DD} = 15 V	T _A = 25°C	14.95	15		
			All other temperatures	14.95			
V _{IL} max	Input low voltage	V _O = 4.5 V, V _{DD} = 5 V, all temperatures				1	
		V _O = 9 V, V _{DD} = 10 V, all temperatures				2	
		V _O = 13.5 V, V _{DD} = 15 V, all temperatures				2.5	
V _{IH} min	Input high voltage	V _O = 0.5 V, V _{DD} = 5 V, all temperatures		4			
		V _O = 1 V, V _{DD} = 10 V, all temperatures		8			
		V _O = 1.5 V, V _{DD} = 15 V, all temperatures		12.5			

Electrical Characteristics – Static (continued)

$T_A = 25^\circ\text{C}$; input $t_r, t_f = 20 \text{ ns}$; $C_L = 50 \text{ pF}$; $R_L = 200 \text{ k}\Omega$ (unless otherwise noted)

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
I_{INmax} Input current	$V_{IN} = 0 \text{ V to } 18 \text{ V}, V_{DD} = 18 \text{ V}$	$T_A = -55^\circ\text{C}$		± 01	μA
		$T_A = -40^\circ\text{C}$		± 01	
		$T_A = 25^\circ\text{C}$		$\pm 10^{-5}$	
		$T_A = 85^\circ\text{C}$		± 1	
		$T_A = 125^\circ\text{C}$		± 1	

6.7 Typical Characteristics

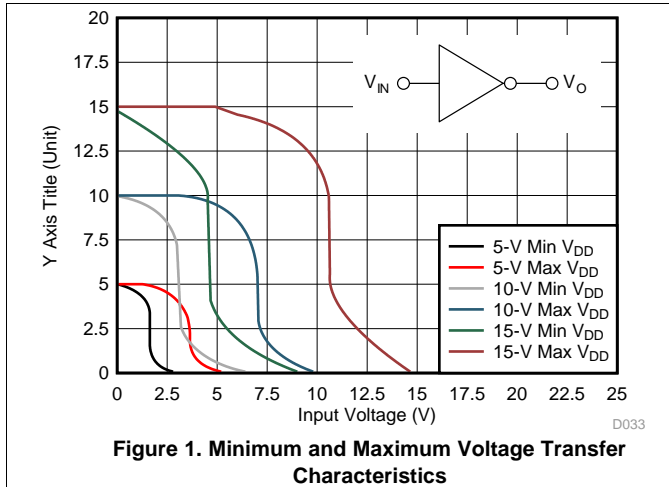


Figure 1. Minimum and Maximum Voltage Transfer Characteristics

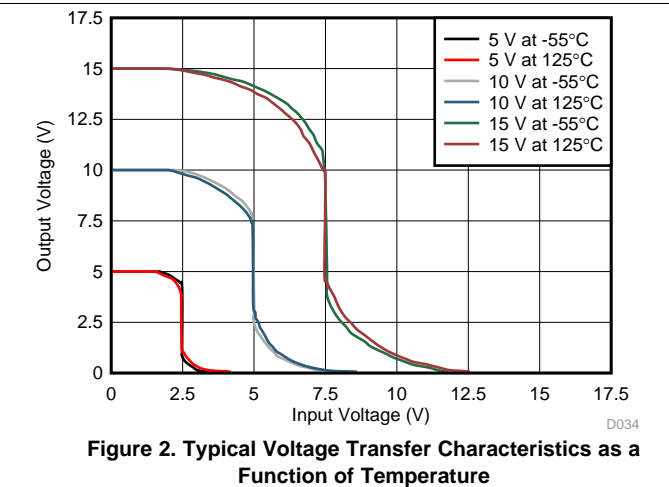


Figure 2. Typical Voltage Transfer Characteristics as a Function of Temperature

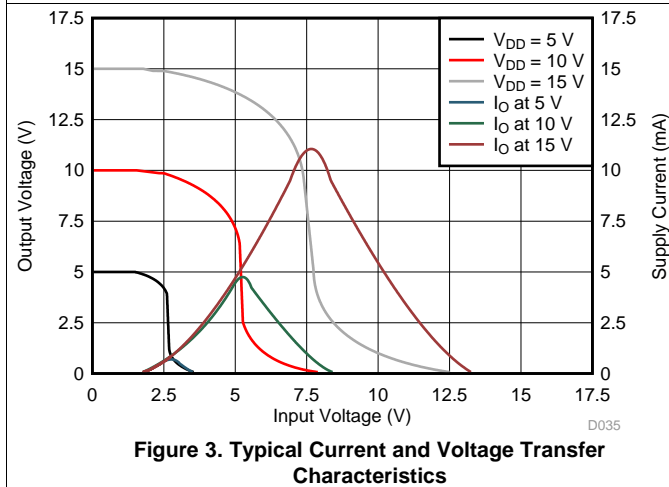


Figure 3. Typical Current and Voltage Transfer Characteristics

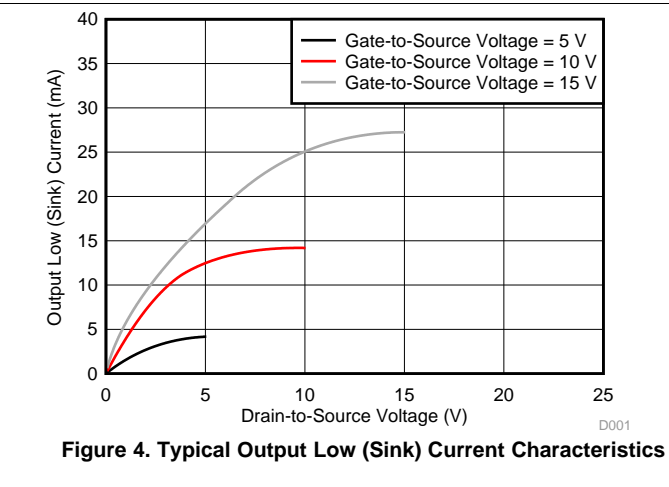


Figure 4. Typical Output Low (Sink) Current Characteristics

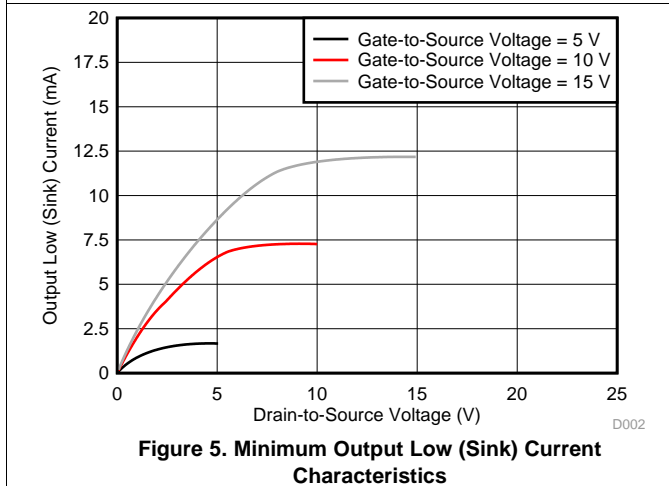


Figure 5. Minimum Output Low (Sink) Current Characteristics

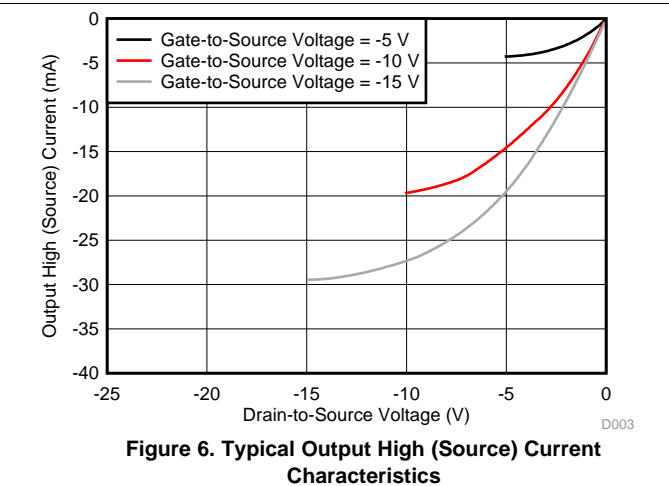
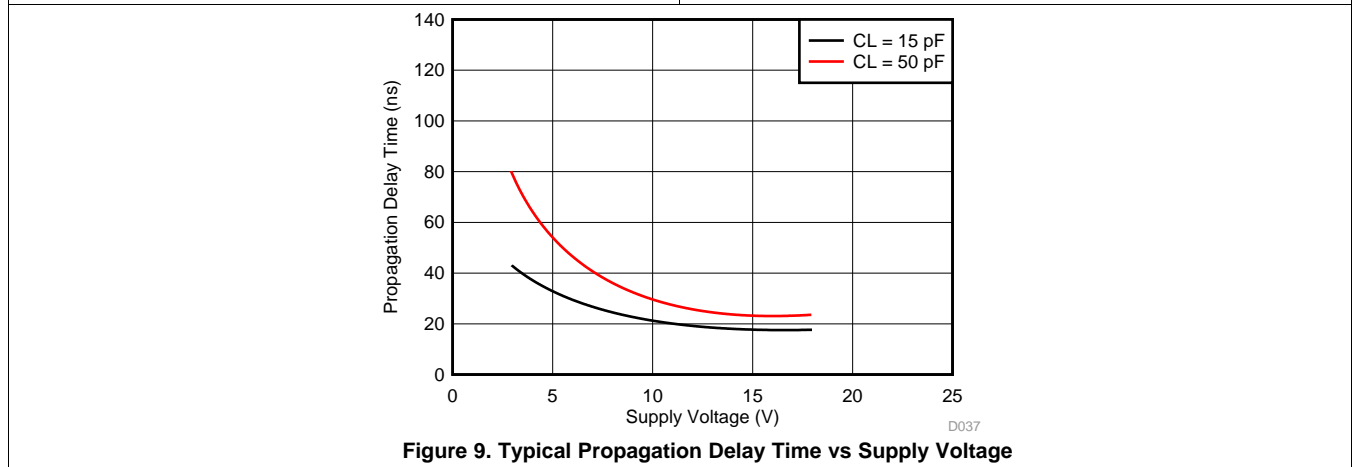
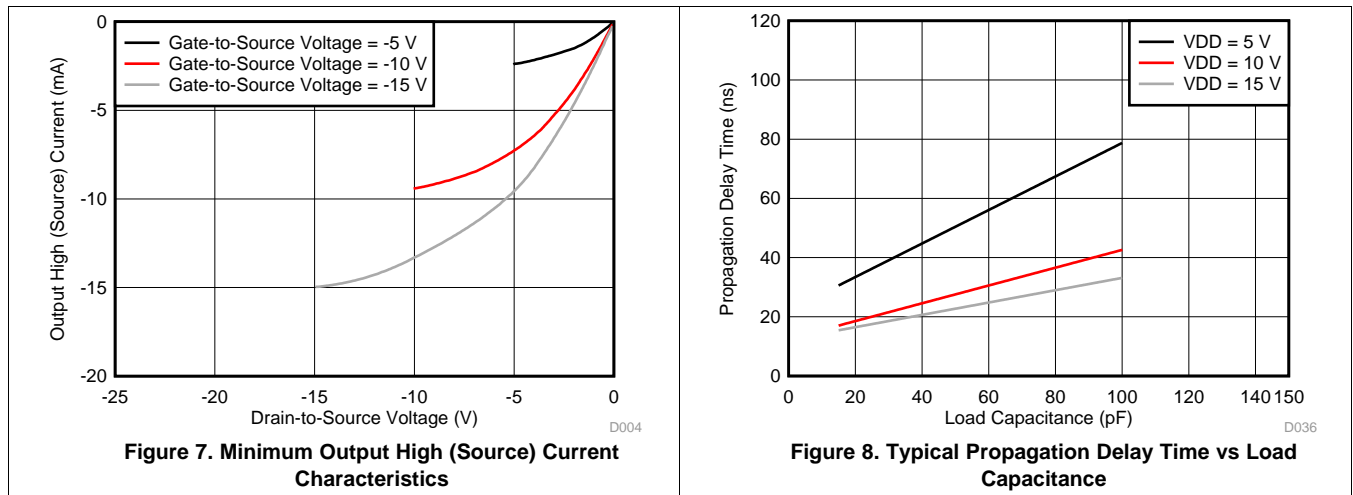


Figure 6. Typical Output High (Source) Current Characteristics

Typical Characteristics (continued)



7 Parameter Measurement Information

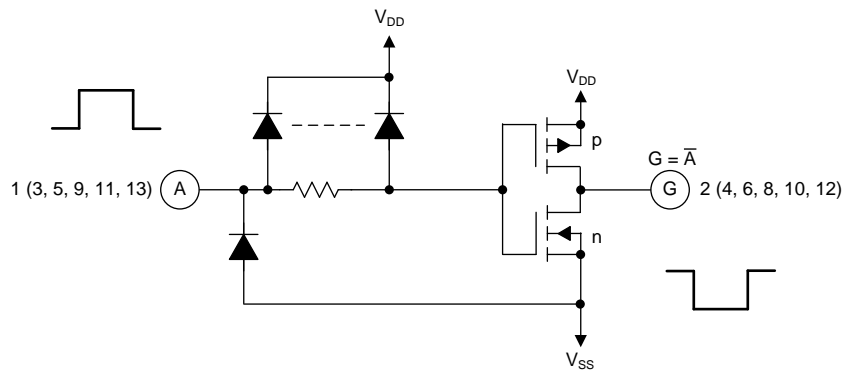


Figure 10. Schematic Diagram of One of Six Identical Inverters

Parameter Measurement Information (continued)

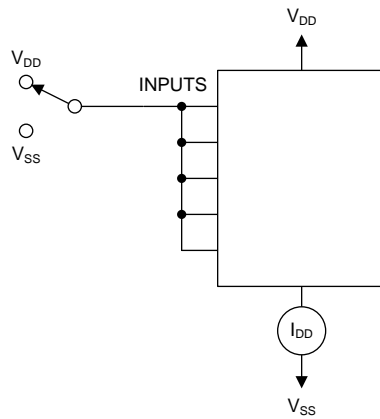


Figure 11. Quiescent Device Current Test Circuit

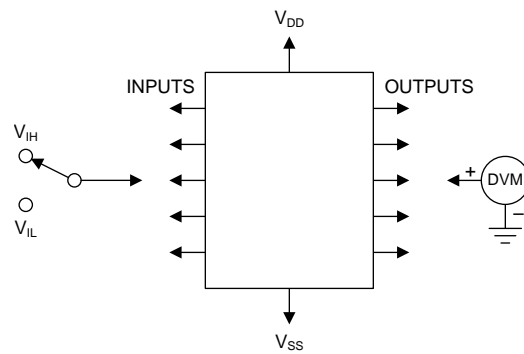


Figure 12. Noise Immunity Test Circuit

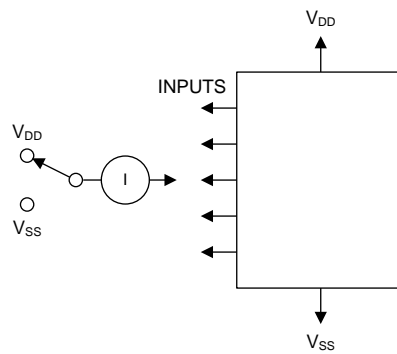


Figure 13. Input Leakage Current Test Circuit

Parameter Measurement Information (continued)

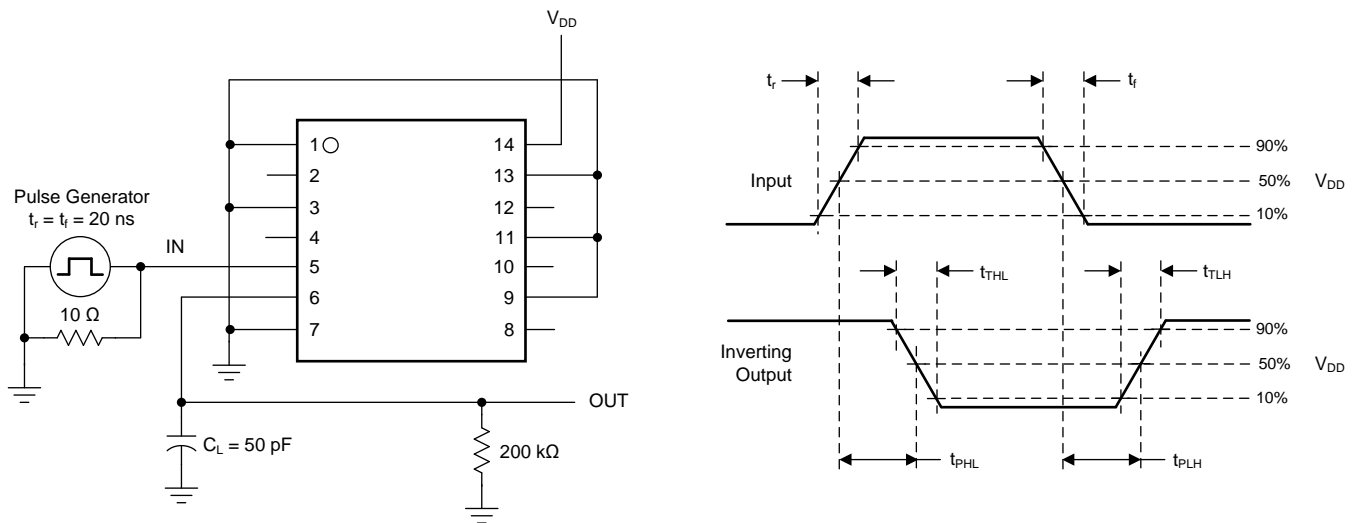


Figure 14. Dynamic Electrical Characteristics Test Circuit and Waveform

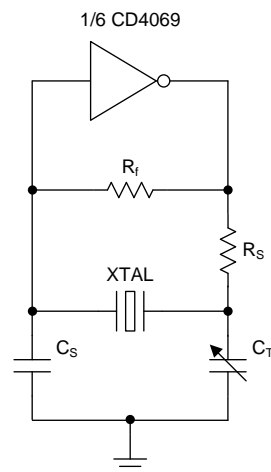


Figure 15. Typical Crystal Oscillator Circuit

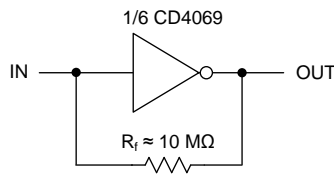


Figure 16. High-Input Impedance Amplifier

Parameter Measurement Information (continued)

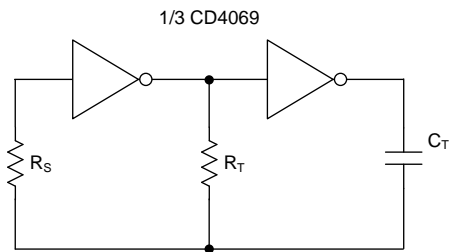
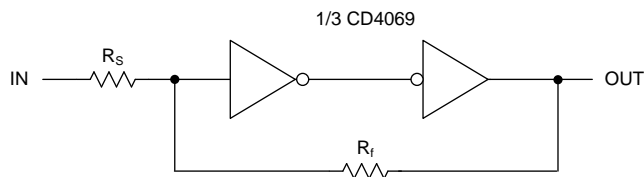


Figure 17. Typical RC Oscillator Circuit



Upper Switching Point :

$$V_P = \frac{R_S + R_f}{R_f} \times \frac{V_{DD}}{2}$$

Lower Switching Point :

$$V_N = \frac{R_f - R_S}{R_f} \times \frac{V_{DD}}{2}$$

$$R_f > R_S$$

Figure 18. Input Pulse Shaping Circuit

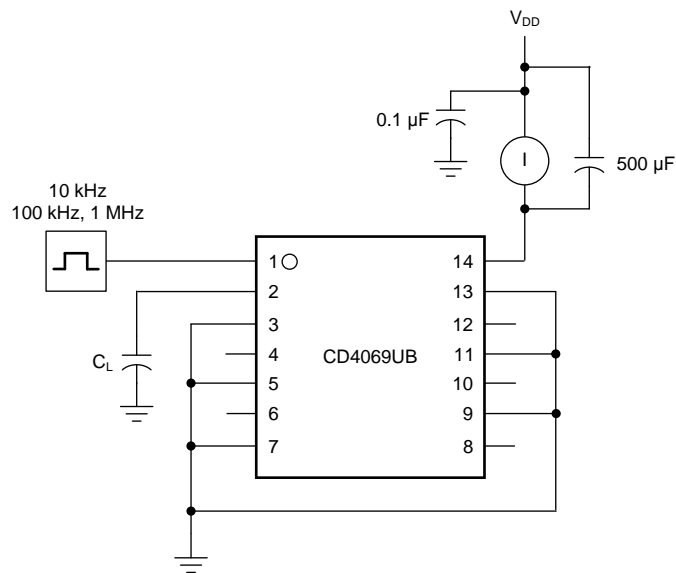


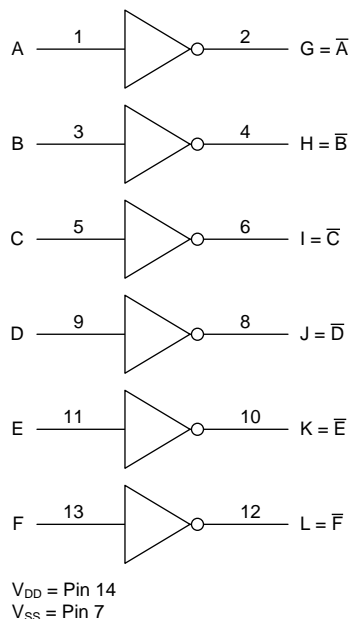
Figure 19. Dynamic Power Dissipation Test Circuit

8 Detailed Description

8.1 Overview

The CD4069UB device has six inverter circuits. The recommended operating range is from 3 V to 18 V. The CD4069UB-series types are supplied in 14-pin hermetic dual-in-line ceramic packages (F3A suffix), 14-pin dual-in-line plastic packages (E suffix), 14-pin small-outline packages (M, MT, M96, and NSR suffixes), and 14-pin thin shrink small-outline packages (PW and PWR suffixes).

8.2 Functional Block Diagram



8.3 Feature Description

CD4069UB has standardized symmetrical output characteristics and a wide operating voltage range from 3 V to 18 V with quiescent current tested at 20 V. This has a medium operation speed $-t_{PHL}$, $t_{PLH} = 30$ ns (typical) at 10 V. The operating temperature is from -55°C to 125°C . CD4069UB meets all requirements of JEDEC tentative standard No. 13B, *Standard Specifications for Description of B Series CMOS Devices*.

8.4 Device Functional Modes

Table 1 shows the functional modes for CD4069UB.

Table 1. Function Table

INPUT A, B, C, D, E, F	OUTPUT G, H, I, J, K, L
H	L
L	H

9 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

The CD4069UB device has a low input current of 1 μA at 18 V over full package-temperature range and 100 nA at 18 V, 25°C. This device has a wide operating voltage range from 3 V to 18 V and used in high voltage applications.

9.2 Typical Application

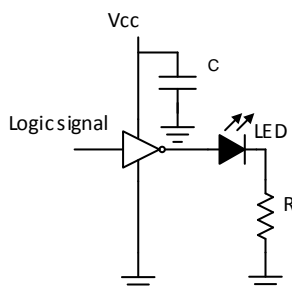


Figure 20. CD4069UB Application

9.2.1 Design Requirements

The CD4069UB device is the industry's highest logic inverter operating at 18 V under recommended conditions. The lower drive capabilities makes it suitable for driving light loads like LED and greatly reduces chances of overshoots and undershoots.

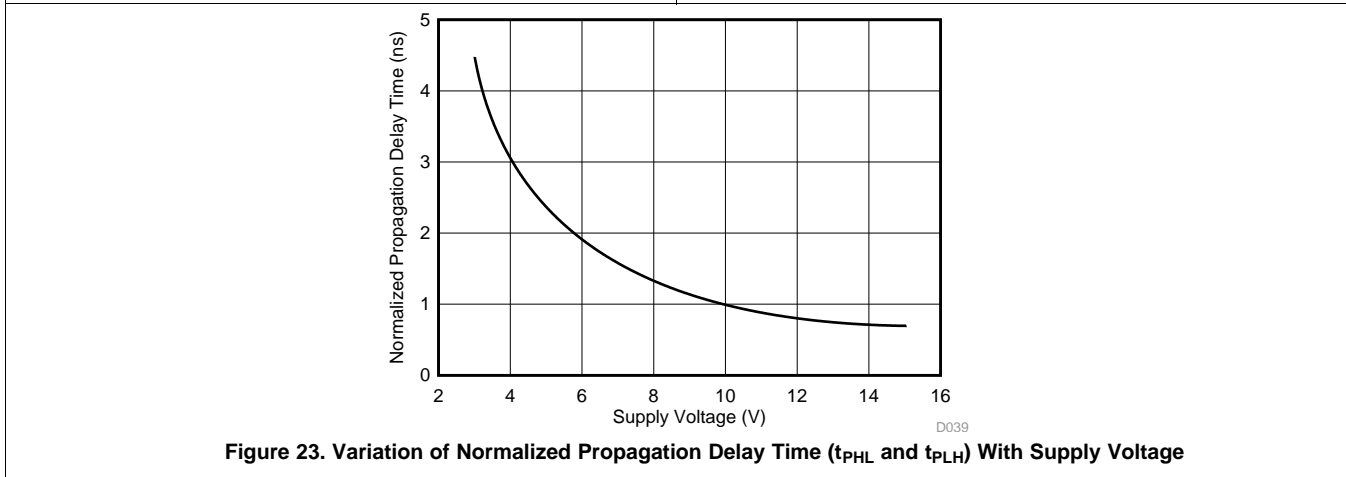
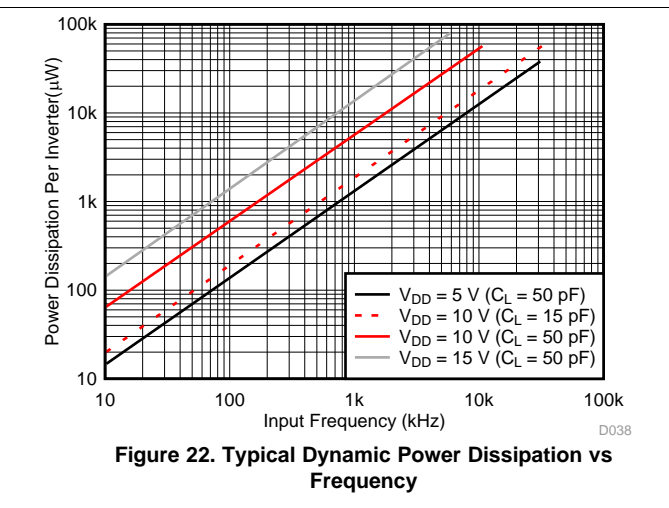
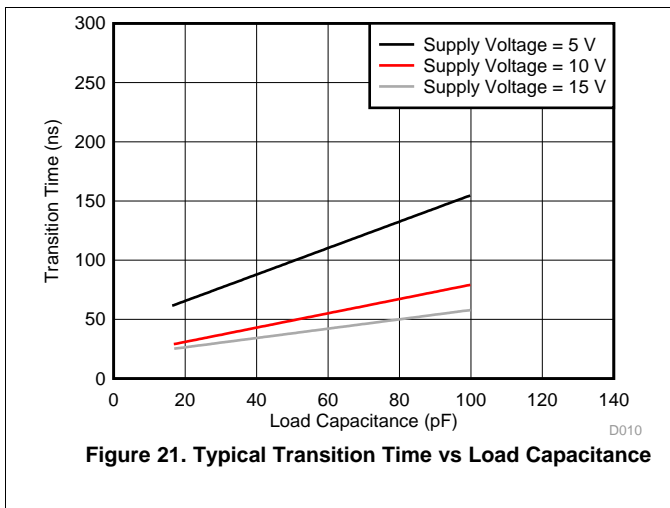
9.2.2 Detailed Design Procedure

The recommended input conditions for [Figure 20](#) includes rise time and fall time specifications (see $\Delta t/\Delta V$ in [Recommended Operating Conditions](#)) and specified high and low levels (see V_{IH} and V_{IL} in [Recommended Operating Conditions](#)). Inputs are not overvoltage tolerant and must be below V_{CC} level because of the presence of input clamp diodes to V_{CC} .

The recommended output condition for the CD4069UB application includes specific load currents. Load currents must be limited so as to not exceed the total power (continuous current through V_{CC} or GND) for the device. These limits are located in the [Absolute Maximum Ratings](#). Outputs must not be pulled above V_{CC} .

Typical Application (continued)

9.2.3 Application Curves



10 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in [Recommended Operating Conditions](#).

Each V_{CC} pin must have a good bypass capacitor to prevent power disturbance. For devices with a single supply, TI recommends a 0.1- μF capacitor. If there are multiple V_{CC} pins, then TI recommends a 0.01- μF or 0.022- μF capacitor for each power pin. It is acceptable to parallel multiple bypass capacitors to reject different frequencies of noise. 0.1- μF and 1- μF capacitors are commonly used in parallel. The bypass capacitor must be installed as close to the power pin as possible for best results.

11 Layout

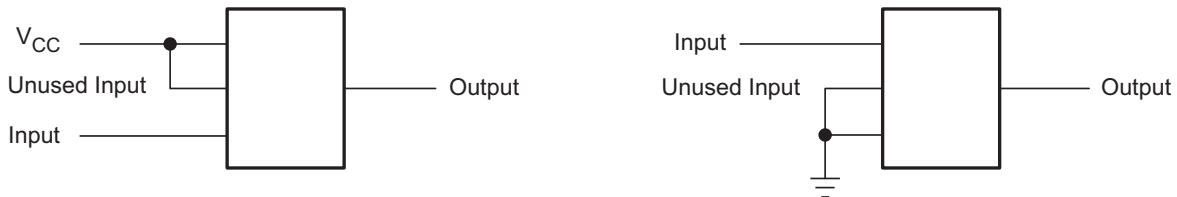
11.1 Layout Guidelines

When using multiple bit logic devices, inputs must never float.

In many cases, digital logic device functions or parts of these functions are unused (for example, when only two inputs of a triple-input and gate are used, or only 3 of the 4 buffer gates are used). Such input pins must not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. This rule must be observed under all circumstances specified in the next paragraph.

All unused inputs of digital logic devices must be connected to a high or low bias to prevent them from floating. See the application note, [Implications of Slow or Floating CMOS Inputs \(SCBA004\)](#), for more information on the effects of floating inputs. The logic level must apply to any particular unused input depending on the function of the device. Generally, they are tied to GND or V_{CC} (whichever is convenient).

11.2 Layout Example



PACKAGE OPTION ADDENDUM

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
CD4069UBE	ACTIVE	PDIP	N	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	-55 to 125	CD4069UBE	Samples
CD4069UBEE4	ACTIVE	PDIP	N	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	-55 to 125	CD4069UBE	Samples
CD4069UBF	ACTIVE	CDIP	J	14	1	TBD	A42	N / A for Pkg Type	-55 to 125	CD4069UBF	Samples
CD4069UBF3A	ACTIVE	CDIP	J	14	1	TBD	A42	N / A for Pkg Type	-55 to 125	CD4069UBF3A	Samples
CD4069UBM	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-55 to 125	CD4069UBM	Samples
CD4069UBM96	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU CU SN	Level-1-260C-UNLIM	-55 to 125	CD4069UBM	Samples
CD4069UBMG4	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-55 to 125	CD4069UBM	Samples
CD4069UBMT	ACTIVE	SOIC	D	14	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-55 to 125	CD4069UBM	Samples
CD4069UBNSR	ACTIVE	SO	NS	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-55 to 125	CD4069UB	Samples
CD4069UBNSRG4	ACTIVE	SO	NS	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-55 to 125	CD4069UB	Samples
CD4069UBPW	ACTIVE	TSSOP	PW	14	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-55 to 125	CM069UB	Samples
CD4069UBPWE4	ACTIVE	TSSOP	PW	14	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-55 to 125	CM069UB	Samples
CD4069UBPWG4	ACTIVE	TSSOP	PW	14	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-55 to 125	CM069UB	Samples
CD4069UBPWR	ACTIVE	TSSOP	PW	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU CU SN	Level-1-260C-UNLIM	-55 to 125	CM069UB	Samples
JM38510/17401BCA	ACTIVE	CDIP	J	14	1	TBD	A42	N / A for Pkg Type	-55 to 125	JM38510/17401BCA	Samples
M38510/17401BCA	ACTIVE	CDIP	J	14	1	TBD	A42	N / A for Pkg Type	-55 to 125	JM38510/17401BCA	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) -

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

⁽⁵⁾ Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

⁽⁶⁾ Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

OTHER QUALIFIED VERSIONS OF CD4069UB, CD4069UB-MIL :

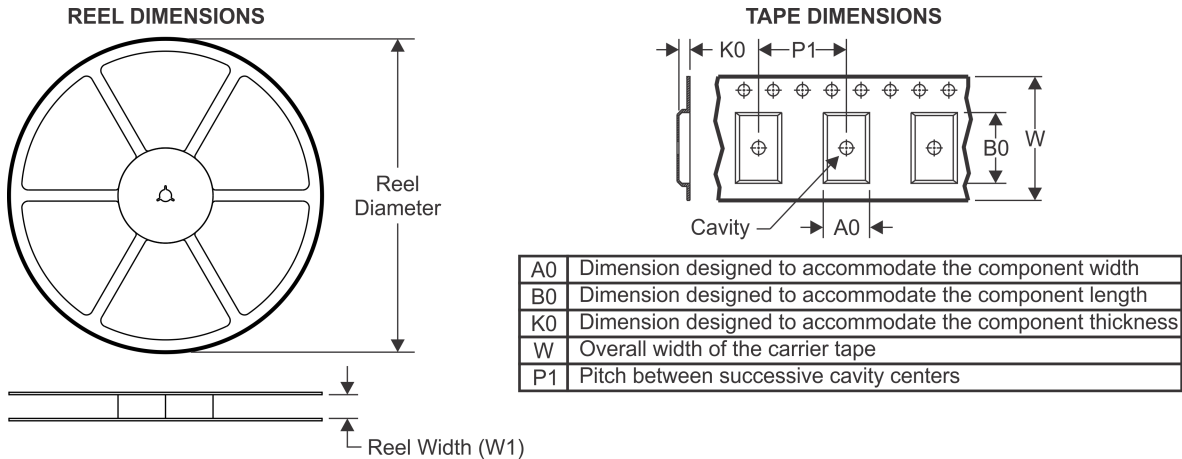
● Catalog: [CD4069UB](#)

● Military: [CD4069UB-MIL](#)

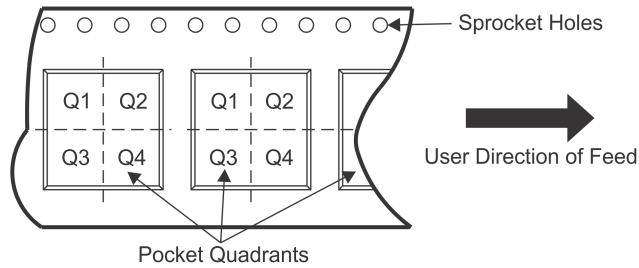
NOTE: Qualified Version Definitions:

PACKAGE MATERIALS INFORMATION

TAPE AND REEL INFORMATION



QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE

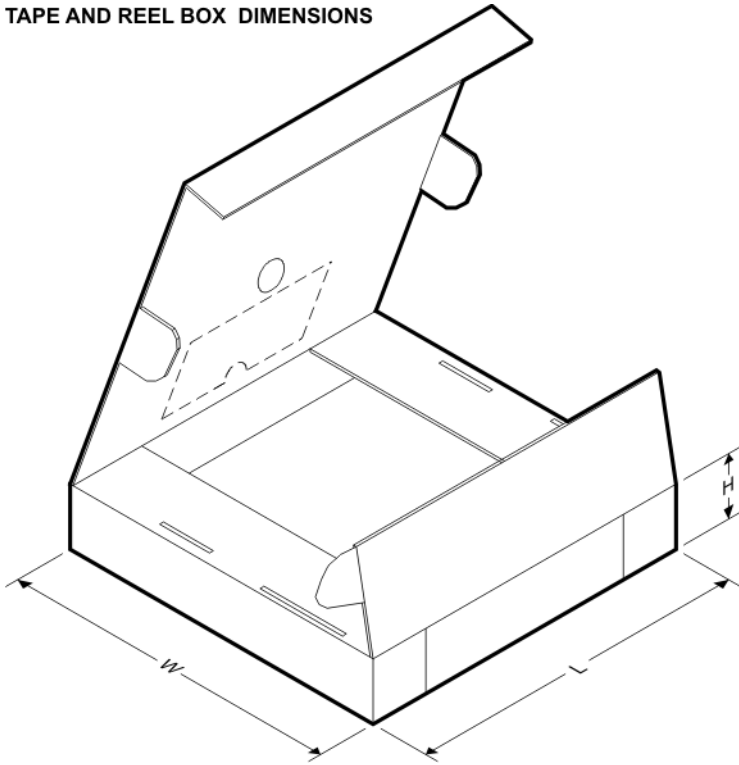


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CD4069UBM96	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
CD4069UBM96	SOIC	D	14	2500	330.0	16.8	6.5	9.5	2.3	8.0	16.0	Q1
CD4069UBMT	SOIC	D	14	250	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
CD4069UBNSR	SO	NS	14	2000	330.0	16.4	8.2	10.5	2.5	12.0	16.0	Q1
CD4069UBPWR	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
CD4069UBPWR	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1

PACKAGE MATERIALS INFORMATION

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

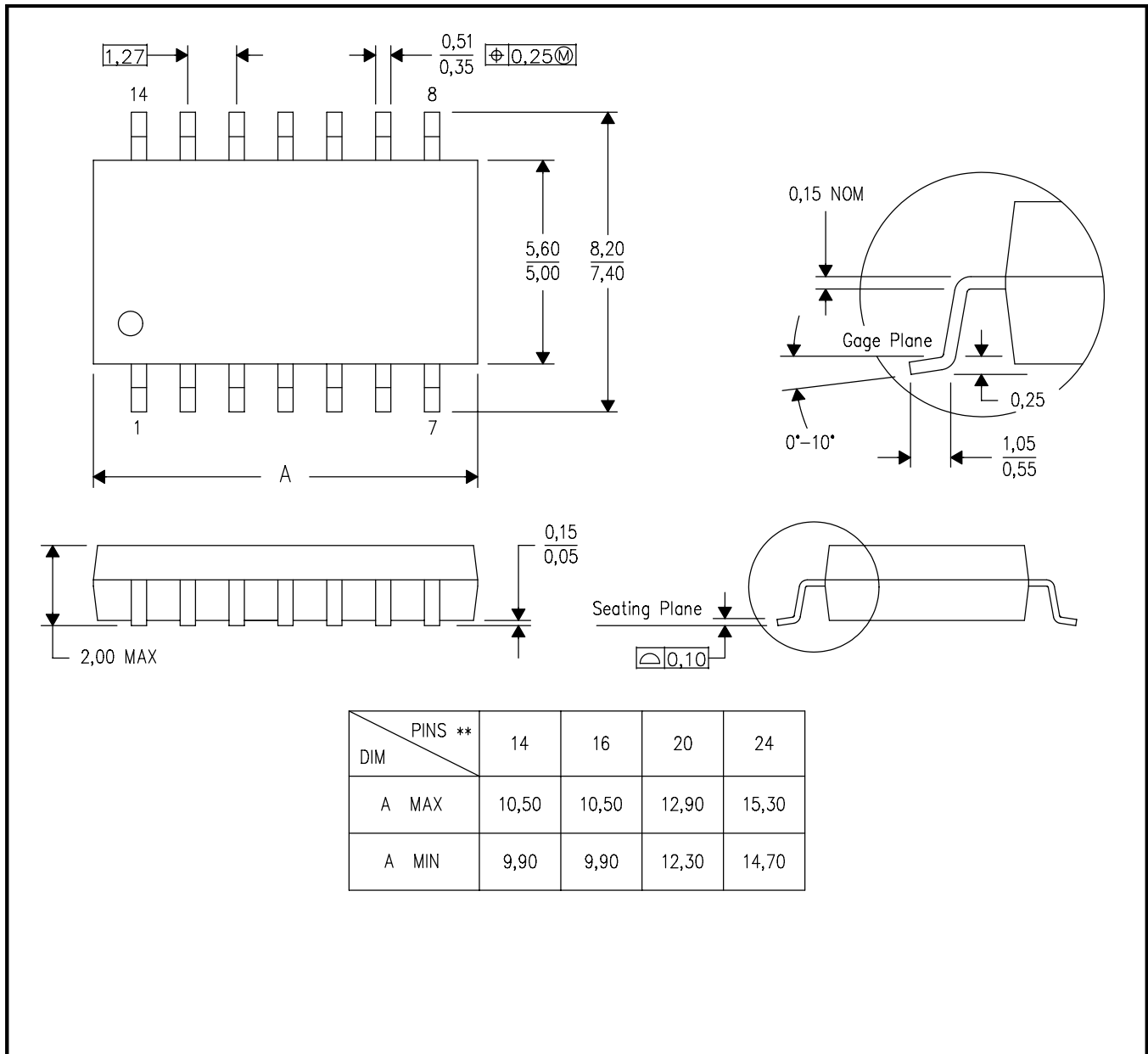
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CD4069UBM96	SOIC	D	14	2500	367.0	367.0	38.0
CD4069UBM96	SOIC	D	14	2500	364.0	364.0	27.0
CD4069UBMT	SOIC	D	14	250	367.0	367.0	38.0
CD4069UBNSR	SO	NS	14	2000	367.0	367.0	38.0
CD4069UBPWR	TSSOP	PW	14	2000	367.0	367.0	35.0
CD4069UBPWR	TSSOP	PW	14	2000	364.0	364.0	27.0

MECHANICAL DATA

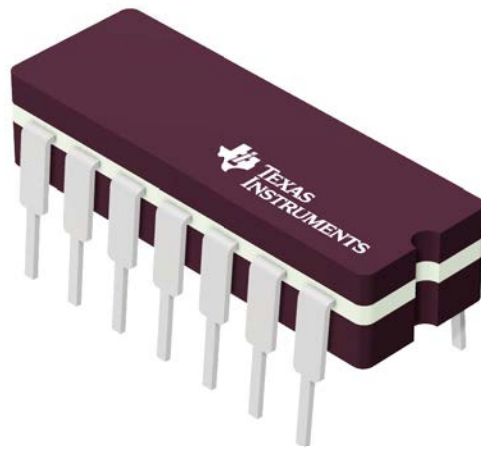
NS (R-PDSO-G)**

PLASTIC SMALL-OUTLINE PACKAGE

14-PINS SHOWN

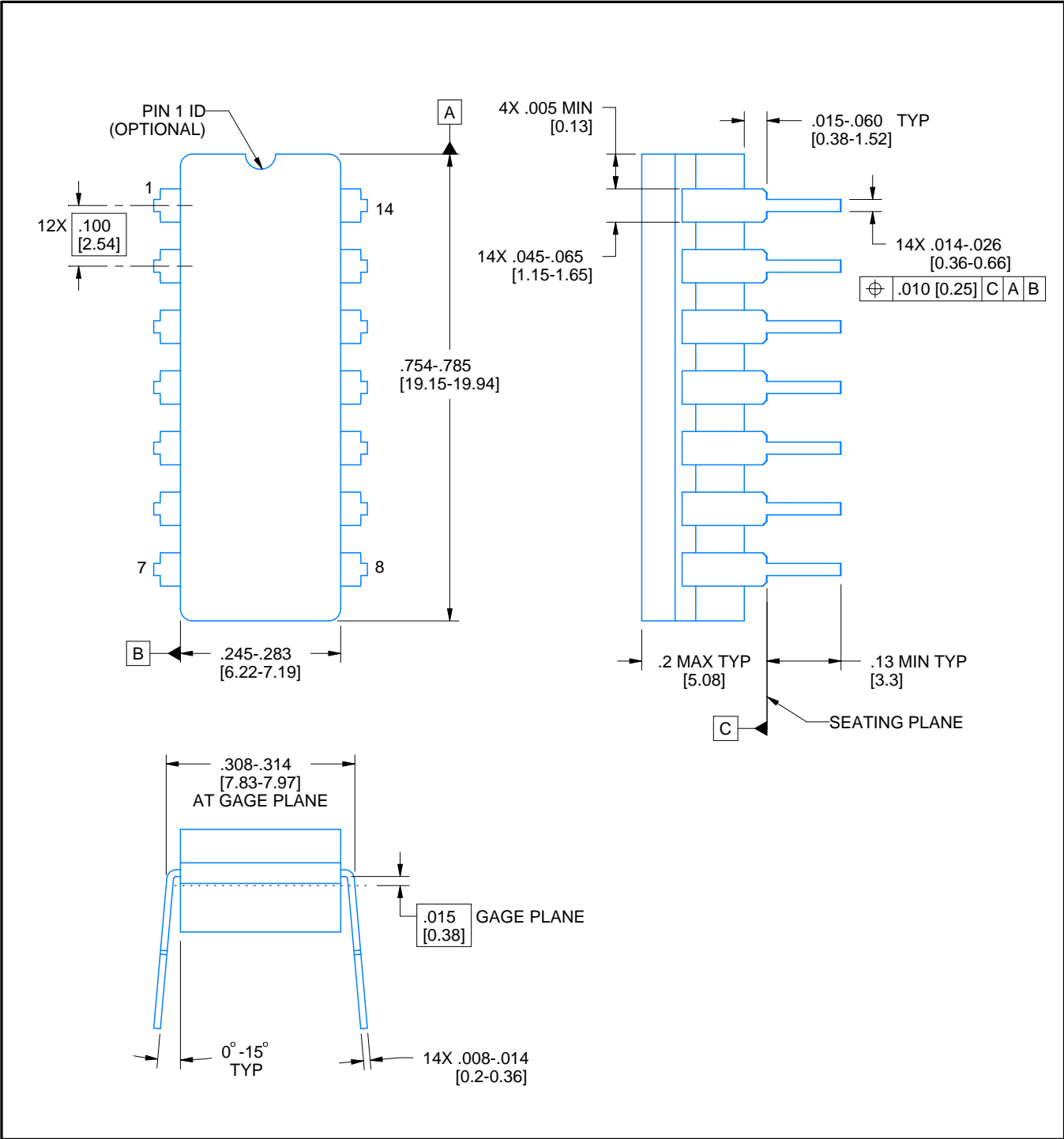


- NOTES:
- A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15.



Images above are just a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.

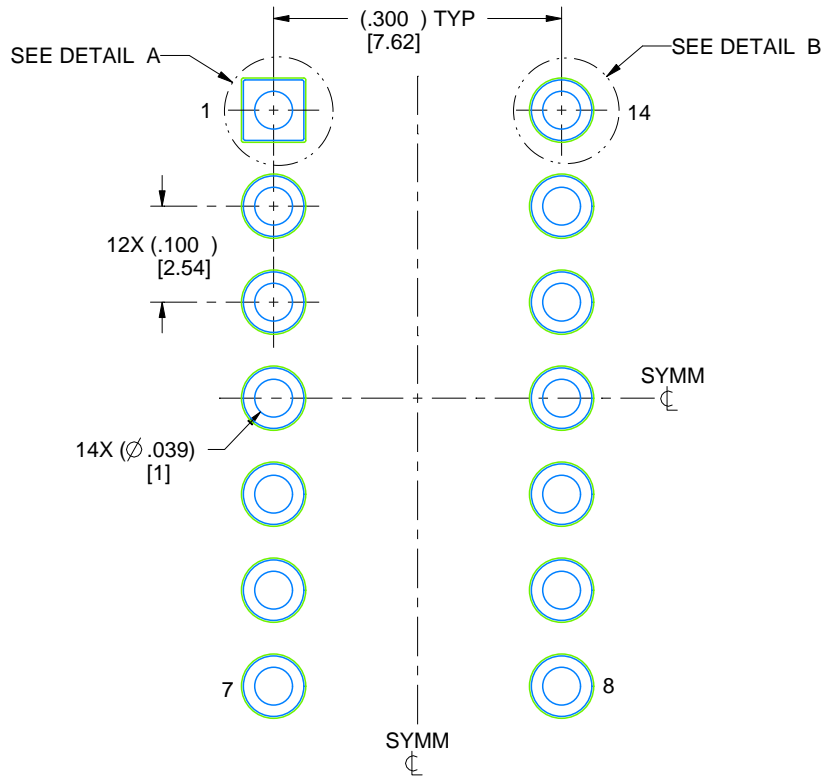
PACKAGE OUTLINE



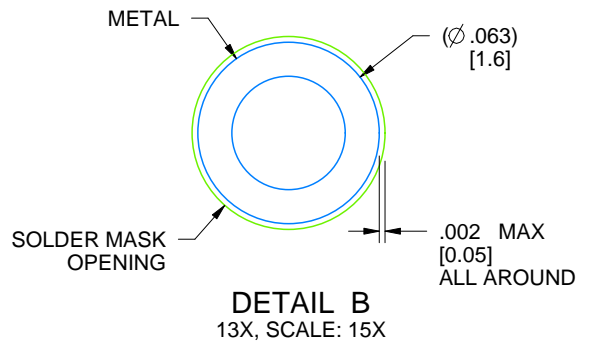
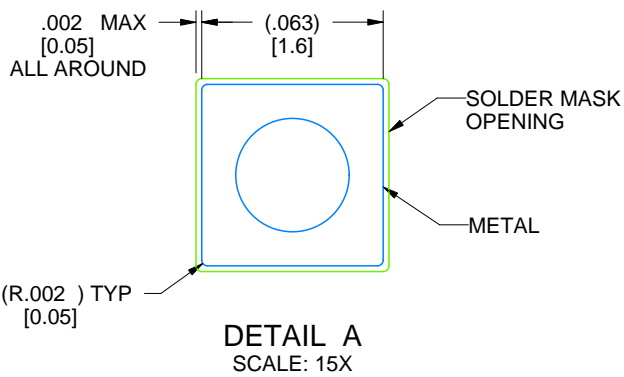
NOTES:

1. All controlling linear dimensions are in inches. Dimensions in brackets are in millimeters. Any dimension in brackets or parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This package is hermetically sealed with a ceramic lid using glass frit.
4. Index point is provided on cap for terminal identification only and on press ceramic glass frit seal only.
5. Falls within MIL-STD-1835 and GDIP1-T14.

EXAMPLE BOARD LAYOUT

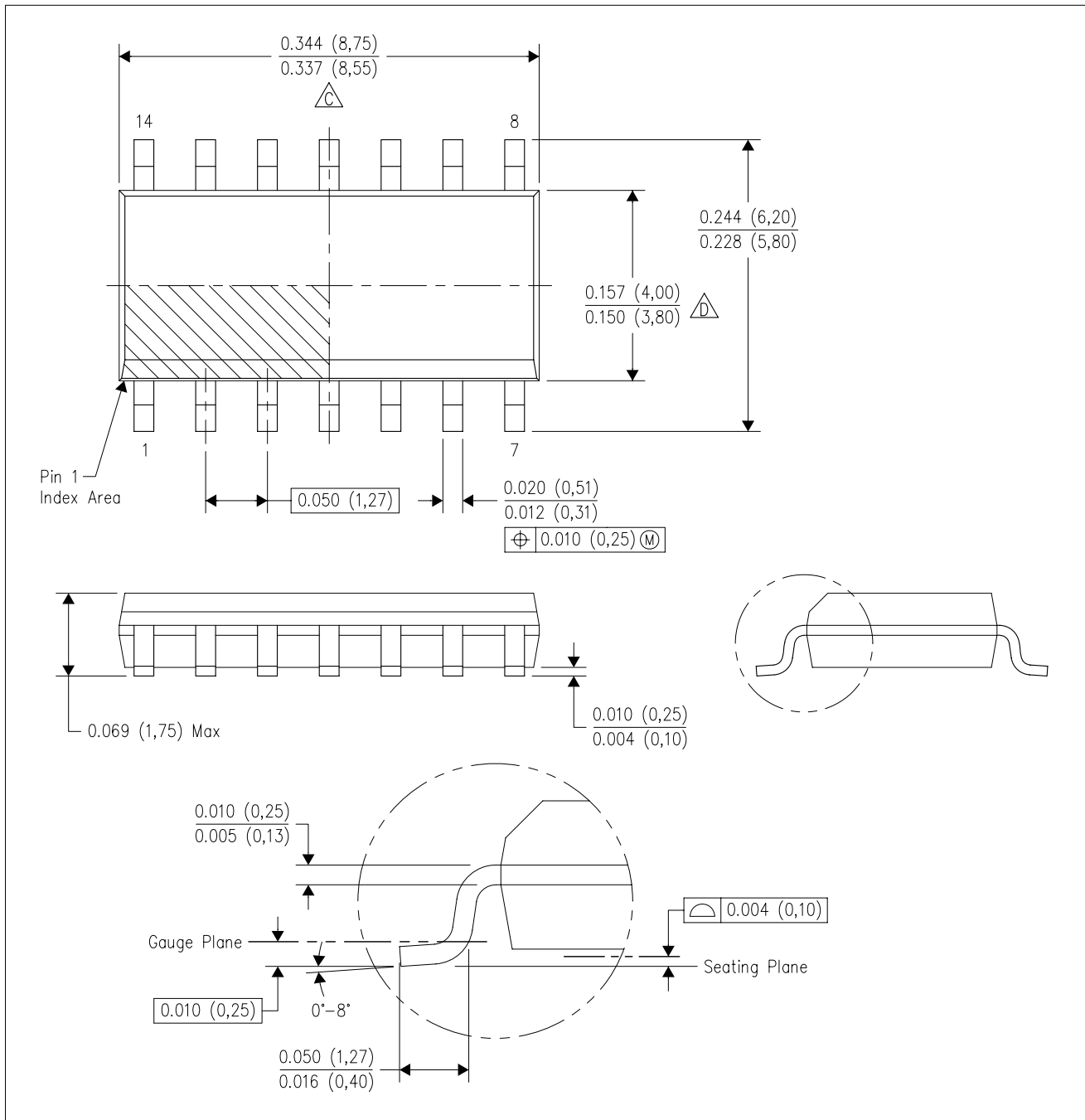


LAND PATTERN EXAMPLE
NON-SOLDER MASK DEFINED
SCALE: 5X



D (R-PDSO-G14)

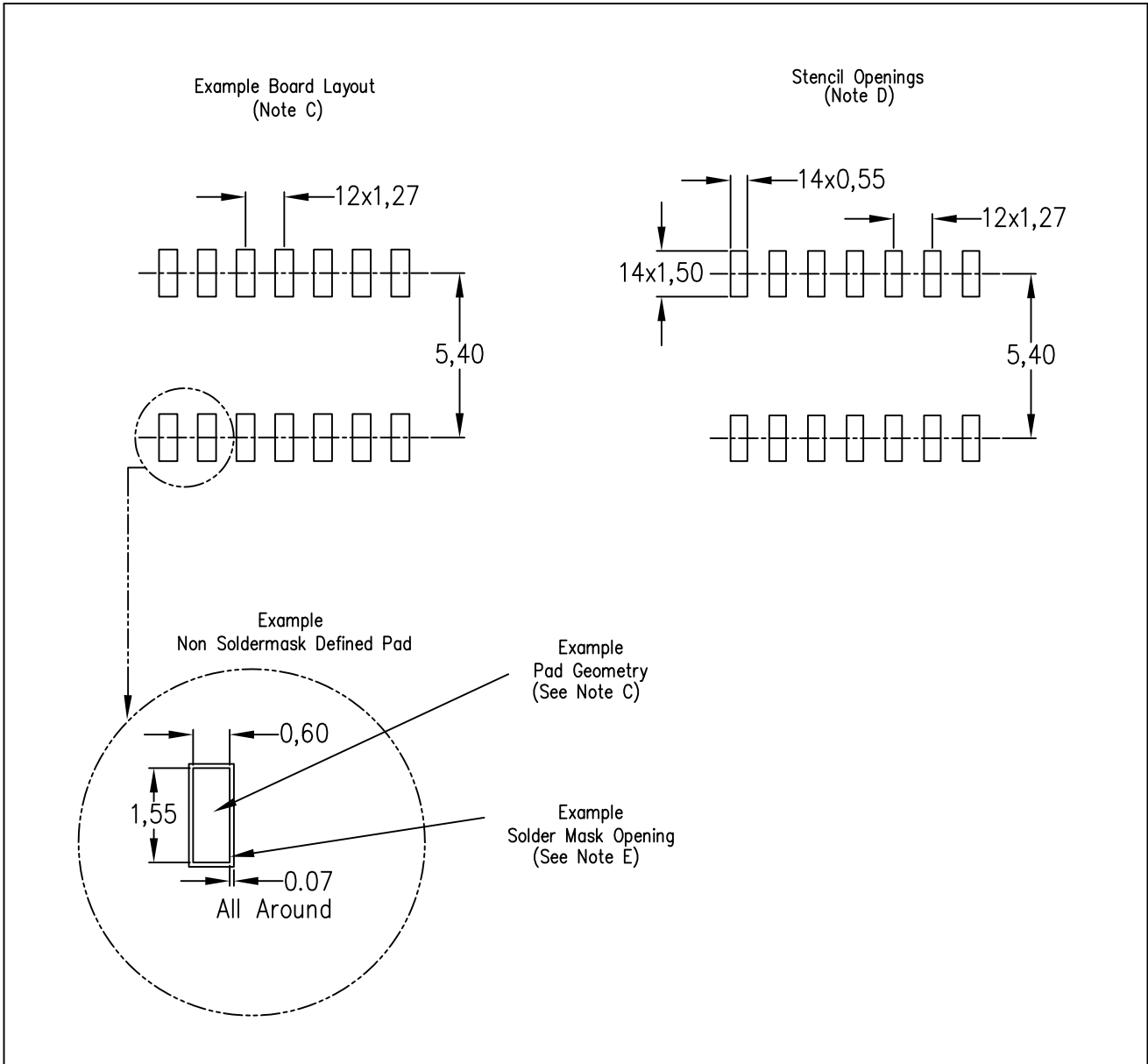
PLASTIC SMALL OUTLINE



- NOTES:
- A. All linear dimensions are in inches (millimeters).
 - B. This drawing is subject to change without notice.
 - $\triangle C$ Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
 - $\triangle D$ Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
 - E. Reference JEDEC MS-012 variation AB.

D (R-PDSO-G14)

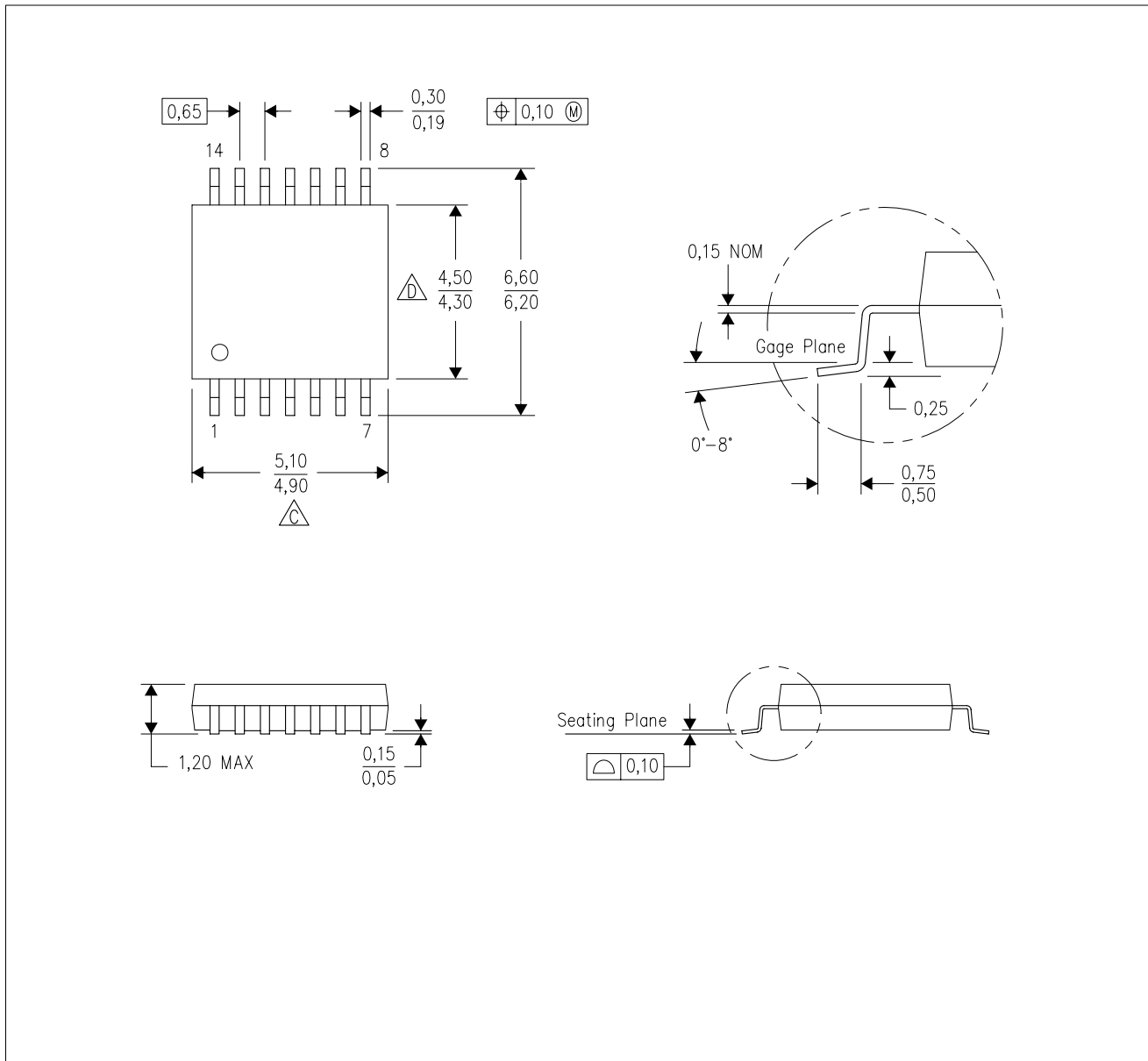
PLASTIC SMALL OUTLINE





- NOTES:
- A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. Publication IPC-7351 is recommended for alternate designs.
 - D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
 - E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

PW (R-PDSO-G14)

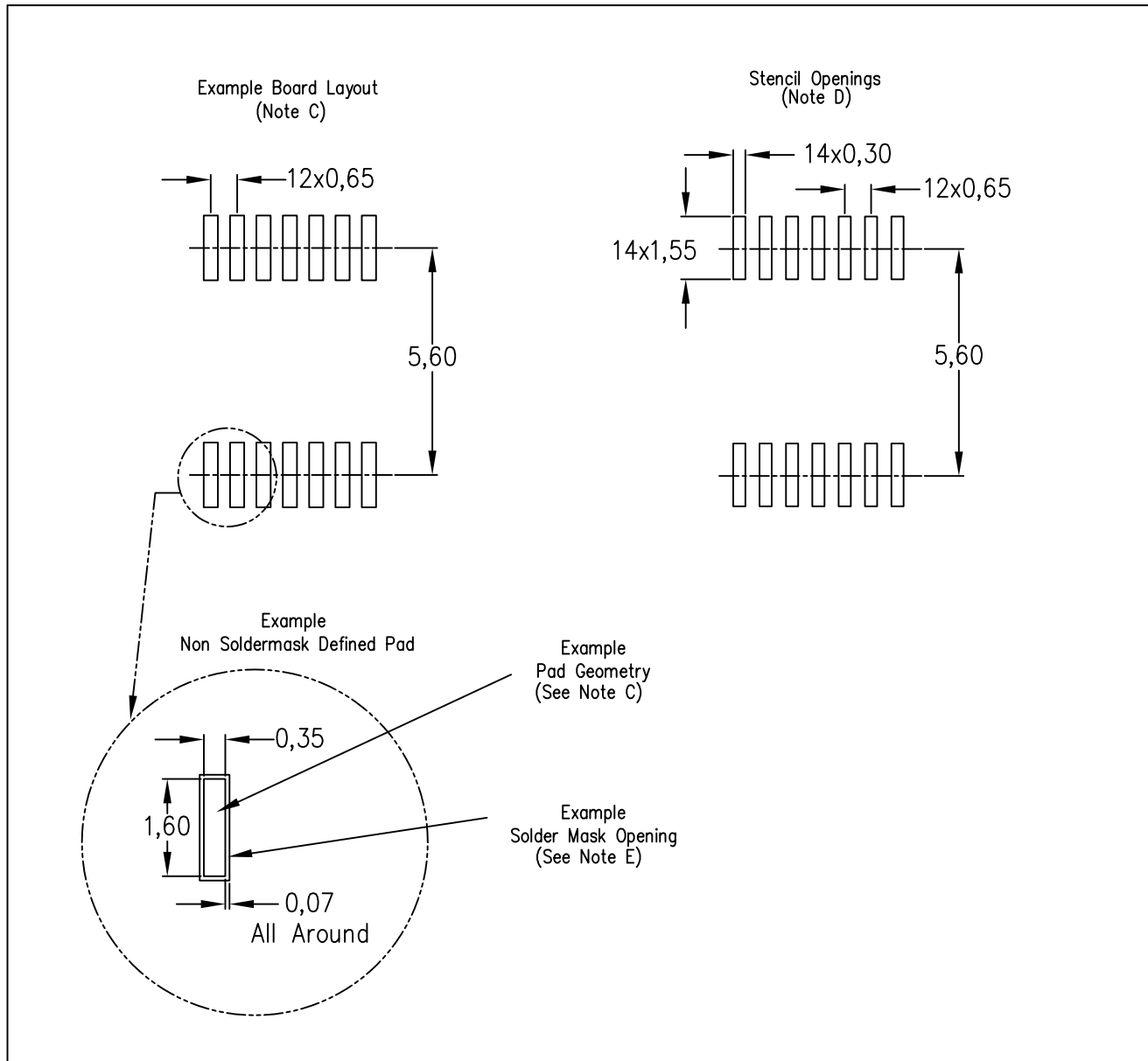
PLASTIC SMALL OUTLINE



- NOTES:
- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.
 - B. This drawing is subject to change without notice.
 -  Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0,15 each side.
 -  Body width does not include interlead flash. Interlead flash shall not exceed 0,25 each side.
 - E. Falls within JEDEC MO-153

PW (R-PDSO-G14)

PLASTIC SMALL OUTLINE

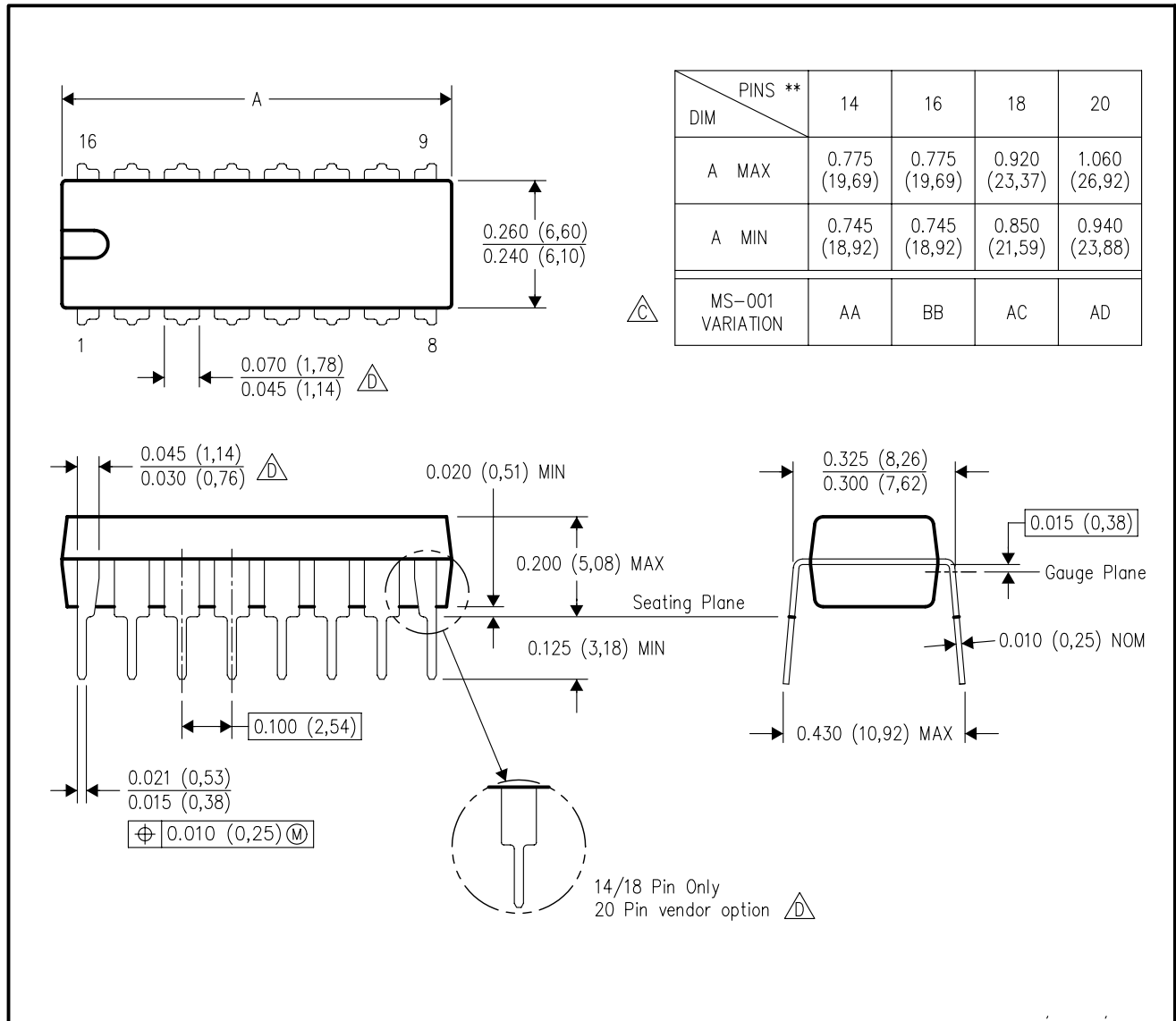


- NOTES:
- All linear dimensions are in millimeters.
 - This drawing is subject to change without notice.
 - Publication IPC-7351 is recommended for alternate designs.
 - Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
 - Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

N (R-PDIP-T**)

PLASTIC DUAL-IN-LINE PACKAGE

16 PINS SHOWN



- NOTES:
- A. All linear dimensions are in inches (millimeters).
 - B. This drawing is subject to change without notice.
 - Falls within JEDEC MS-001, except 18 and 20 pin minimum body length (Dim A).
 - The 20 pin end lead shoulder width is a vendor option, either half or full width.